



Silicon Super Fast Recovery Diode

MUR20005CT thru MUR20020CTR

$V_{RRM} = 50\text{ V} - 600\text{ V}$

$I_F = 200\text{ A}$

Features

- High Surge Capability
- Types up to 600 V V_{RRM}

Twin Tower Package



Maximum ratings, at $T_j = 25\text{ °C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MUR20005CT (R)	MUR20010CT (R)	MUR20020CT (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		50	100	200	V
RMS reverse voltage	V_{RMS}		35	70	140	V
DC blocking voltage	V_{DC}		50	100	200	V
Continuous forward current	I_F	$T_C \leq 140\text{ °C}$	200	200	200	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$, $t_p = 8.3\text{ ms}$	800	800	800	A
Operating temperature	T_j		-40 to 175	-40 to 175	-40 to 175	°C
Storage temperature	T_{stg}		-40 to 175	-40 to 175	-40 to 175	°C

Electrical characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	MUR20005CT (R)	MUR20010CT (R)	MUR20020CT (R)	Unit
Diode forward voltage	V _F	I _F = 100 A, T _j = 25 °C	1.3	1.3	1.3	V
Reverse current	I _R	V _R = 50 V, T _j = 25 °C	25	25	25	μA
		V _R = 50 V, T _j = 125 °C	1	1	1	mA
Recovery Time						
Maximum reverse recovery time	T _{RR}	I _F =0.5 A, I _R =1.0 A, I _{RR} = 0.25 A	75	75	75	nS





America Semiconductor

MUR20005CT thru MUR20020CTR

